

Monolithic Dual Switching Diode Common Cathode

● FEATURES

- 1) We declare that the material of product compliant with RoHS requirements and Halogen Free.
- 2) S- Prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.

● DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LBAV70LT1G	A4	3000/Tape&Reel
LBAV70LT3G	A4	10000/Tape&Reel

● MAXIMUM RATINGS($T_a = 25^\circ C$)

Parameter	Symbol	Limits	Unit
Reverse Voltage	V_R	70	Vdc
Forward Current	I_F	200	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	500	mAdc

● THERMAL CHARACTERISTICS

Parameter	Symbol	Symbol	Max.	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ C$		P_D	225	mW
Derate above $25^\circ C$			1.8	$mW/^\circ C$
Thermal Resistance Junction to Ambient	$R_{\theta JA}$		556	$^\circ C/W$
Total Device Dissipation Alumina Substrate (Note 2) $T_A = 25^\circ C$		P_D	300	mW
Derate above $25^\circ C$			2.4	$mW/^\circ C$
Thermal Resistance Junction to Ambient	$R_{\theta JA}$		417	$^\circ C/W$
Junction and Storage Temperature	T_J, T_{stg}		-55 to +150	$^\circ C$

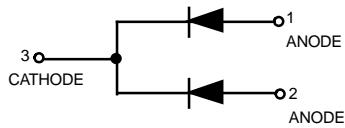
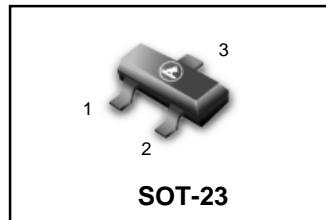
● ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Min	Max.	Unit
Reverse Breakdown Voltage ($I_{(BR)} = 100\mu A$)	$V_{(BR)}$	70	—	Vdc
Reverse Voltage Leakage Current ($V_R = 25$ Vdc, $T_J = 150^\circ C$)	I_R	—	60	uAdc
($V_R = 70$ Vdc)		—	2.5	
($V_R = 70$ Vdc, $T_J = 150^\circ C$)		—	100	
Diode Capacitance ($V_R = 0$, $f = 1.0$ MHz)	C_D	—	1.5	pF
Forward Voltage ($I_F = 1.0$ mAdc) ($I_F = 10$ mAdc)	V_F	—	715	mVdc
($I_F = 50$ mAdc)		—	855	
($I_F = 150$ mAdc)		—	1000	
Reverse Recovery Time (Figure 1) $I_F = I_R = 10$ mAdc, $i_{R(REC)} = 1.0$ mAdc, $R_L = 100 \Omega$	trr	—	1250	
Reverse Recovery Time (Figure 1) $I_F = I_R = 10$ mAdc, $i_{R(REC)} = 1.0$ mAdc, $R_L = 100 \Omega$	trr	—	6	ns

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.

2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.

LBAV70LT1G S-LBAV70LT1G



LBAV70LT1G, S-LBAV70LT1G

ELECTRICAL CHARACTERISTIC CURVES

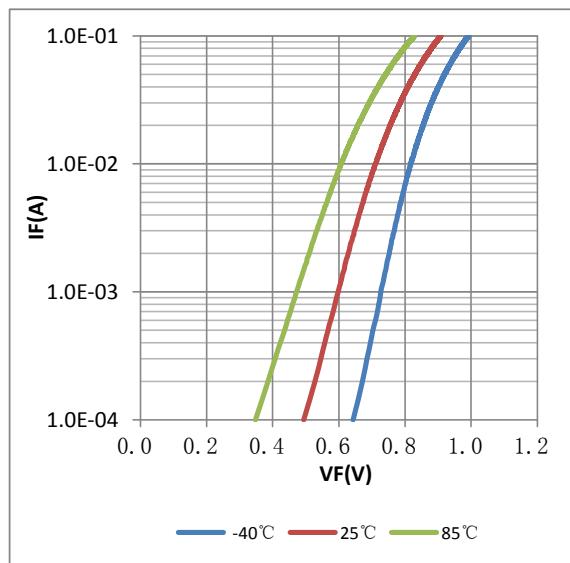


FIG. 1 Forward Characteristics

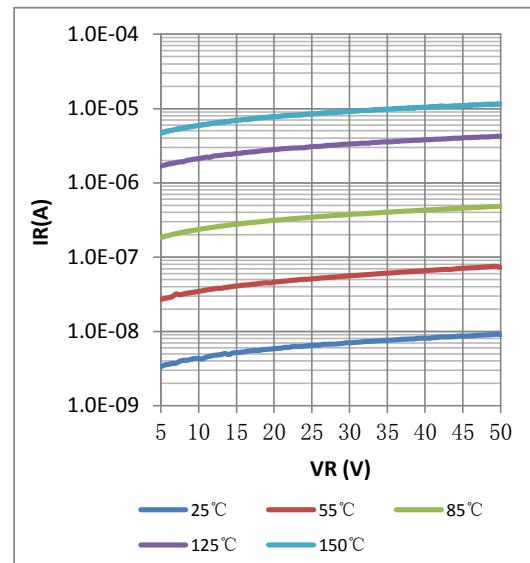


FIG. 2 Reverse Characteristics

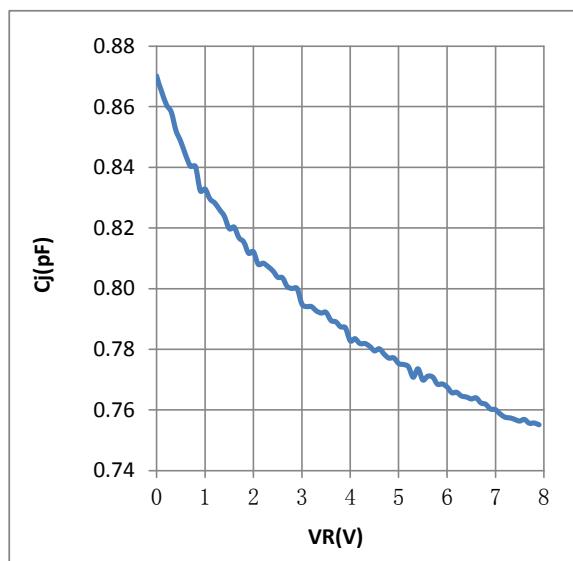
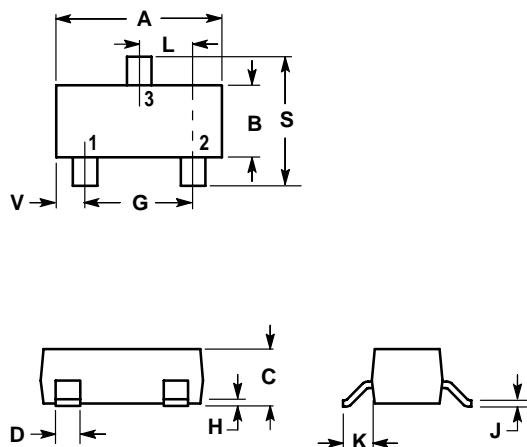


FIG. 3 Capacitance

LBAV70LT1G, S-LBAV70LT1G

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NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

